

# EAST Search History

(8pp) *[Signature]*

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1620	((257/1) or (257/15) or (257/28) or (257/658) or (429/41)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/09 17:27
L2	31	1 and (nano adj particle nanoparticle nano-particle nano adj size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/09 17:28
L3	0	(chang\$3 near2 cho).in. and (nano adj particle nanoparticle nano-particle nano adj size).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/09 17:29
S1	1	(nano-size nano) adj2 particles and electromotive adj force.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:14
S2	71	thermodynamic adj force and thermodynamic flux and electromotive adj force and peltier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:16
S3	44	thermodynamic adj force and thermodynamic flux and electromotive adj force and peltier and current adj source and energy adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:16
S4	44	thermodynamic adj force and thermodynamic flux and electromotive adj force and peltier and current adj source and energy adj source.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:22
S5	163	battery and nanoparticle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:22
S6	34	battery.ti,ab,clm. and nanoparticle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:23

## EAST Search History

S7	4	battery.ti. and nanoparticle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:26
S8	407	(429/41).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/05/02 15:27
S9	5	S8 and (nano adj particle nanoparticle nano-particle nano adj size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/02 15:29
S10	872	((257/1) or (257/15) or (257/58) or (257/658)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:29
S11	1	S10 and (nano adj particle nanoparticle nano-particle nano adj size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/09 17:27
S12	257	((((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/09 17:27
S13	17	((((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor adj (layer or film) and ((second or top or cathode) near1 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/08 21:49
S14	39	((((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor adj (layer or film or substrate) and ((second or top or cathode) near1 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/08 21:50
S15	7	((((dopant or doped) near2 (tantalum nitride or tan)) same (layer or film)) and dielectric and semiconductor adj (layer or film or substrate) and ((second or top or cathode) near1 electrode) and (metal near2 (dopant or doped) or metal-doped or metal-dopant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/08 21:55

## EAST Search History

S16	62	(tan or tantalum adj nitride) and (insulator or dielectric or glass) and semiconductor and ((cathode or upper or top) near3 electrode) and light-emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/08 22:41
S17	18	depletion adj region near12 doping adj profile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/08 22:41
S18	347	metal-doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:20
S19	19	metal-doped and ("257"/\$6.ccls. or "438"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:21
S20	12	metal-doped and ("257"/\$6.ccls. or "438"/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:35
S21	3	metal-doped and ("257"/\$6.ccls. or "438"/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode) and ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:22
S22	109	(metal-doped or conducting adj polymer) and ("257"/\$6.ccls. or "438"/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:36
S23	23	(metal-doped or conducting adj polymer) and ("257"/\$6.ccls. or "438"/\$6.ccls.) and semiconductor and (dielectric or insulat\$3) and (plate or electrode) and (multi-layer\$3 or laminat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:41
S24	0	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near1 dop\$3 near3 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and (multi-layer\$3 or laminat\$3) and ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:46

## EAST Search History

S25	0	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and (multi-layer\$3 or laminat\$3) and ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:47
S26	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulat\$3) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:49
S27	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 10:53
S28	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and ((metal near2 (layer or film)) or electrode) and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 10:55
S29	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) adj (layer or film) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 10:56
S30	5	((metal or cu or copper or al or aluminum or tungsten or w or tantalum or ta or ag or silver or au or gold or tin or sn or zinc or zn) near6 dop\$3 near6 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 10:57

## EAST Search History

S31	7	((doped or doping) near2 conducting adj polymer) and semiconductor and (dielectric or insulator or barrier) and electrode and ohmic adj contact	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 11:40
S32	8	((((doped or doping or dopant) near3 (polyacetylene or polyimide or polyethylene or polyaniline)) near6 (conductivity or resistivity)) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 11:43
S33	8	((((doped or doping or dopant) near3 (polyacetylene or polyimide or polyethylene or polyaniline)) near6 (conductivity or resistivity)) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 11:44
S34	1	((((metal near2 (doped or doping or dopant)) near3 (polyacetylene or polyimide or polyethylene or polyaniline)) near6 (conductivity or resistivity)) near12 semiconductor	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 11:46
S35	2	p-type adj polyacetylene with semiconductor.ti,ab.	USPAT; EPO; JPO; IBM_TDB	OR	ON	2002/03/09 11:47
S36	10	superlattice.ti,ab. and (jfet or junction adj field adj effect adj transistor).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 14:56
S37	187	superlattice.ti,ab. and (fet or field adj effect adj transistor).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 14:56
S38	0	((metal near5 insulat\$3) near5 superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 14:58
S39	48	(superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab. and (aluminum or tungsten or copper or tantalum or molybdenum or metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 15:27
S40	21	((superlattice).ti,ab. and (fet or field adj effect adj transistor).ti,ab. and (aluminum or tungsten or copper or tantalum or molybdenum or metal)) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 16:19

## EAST Search History

S41	11	257/658 and (jfet or fet or field adj effect transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 16:22
S42	0	257/658 and (jfet or fet or field adj effect transistor) and superlattice	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 16:22
S43	350	257/658	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 16:33
S44	224	257/9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 16:39
S45	435	257/15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/03/09 16:40
S46	78	(257/28).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/09 17:13
S47	1	("5250388").PN.	USPAT; USOCR	OR	OFF	2002/03/13 19:54
S48	1	("5049951").PN.	USPAT; USOCR	OR	OFF	2002/03/13 19:54
S49	4	"914103".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/03 15:31
S50	4	"914103".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/04 12:36
S51	0	monolayer near12 metal adj particle near12 nano\$7 and rectifier and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/04 12:37

## EAST Search History

S52	0	monolayer near6 metal adj particle and rectifier and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/04 12:38
S53	1	monolayer near6 rectifier and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/04 12:56
S54	86	filed near6 national adj stage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/04 12:57
S55	3742	"[0001]" near16 International	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/04 13:49
S56	64	tin adj dioxide near6 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/04 13:49
S57	0	(rectifier Schottky) near6 (nanoparticle nano-particle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/05 09:21
S58	0	("((thermodynamicthermal)near3equilibrium)near12(dccontinuouscontinuouslysteady-statesteadystationaryconstant)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/07/07 09:07
S59	102	((thermodynamic thermal) near3 equilibrium) near12 (constant steady-state steady stationary stationnary continuous continuously dc) near12 (voltage potential current power energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/07 09:09
S60	0	("tinadioxide").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/01 16:21

## EAST Search History

S61	54309	tin adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/01 16:21
S62	2419	tin adj oxide near4 (dielectric conductor resistivity conductivity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/01 16:22
S63	454	tin adj oxide near4 (dielectric conductor resistivity conductivity).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/01 16:22
S64	203	tin adj oxide near2 (dielectric conductor resistivity conductivity).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/02 15:05